

P-Channel 30 V (D-S) MOSFET



RoHS
COMPLIANT

PRODUCT SUMMARY			
V _{DS} (V)	R _{DS(on)} (mΩ)(Typ.)	I _D (A)	Q _g (Typ.)
- 30	21 at V _{GS} = - 10 V	- 35 ^a	22 nC
	30 at V _{GS} = - 4.5 V	- 25 ^a	

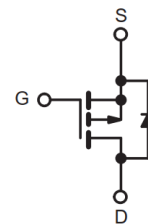
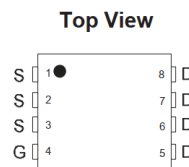
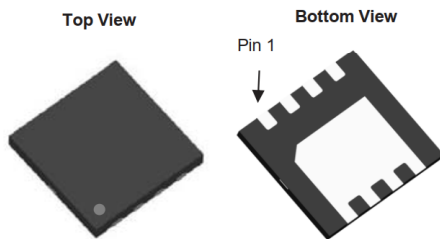
FEATURES

- DT-Trench Power MOSFET
- Thermally Enhanced DFN3X3 Package
- Small Footprint Area
- Low On-Resistance

APPLICATIONS

- Load Switch, PA Switch, and Battery Switch for Portable Devices

DFN3x3-8L



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)			
Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	- 30	V
Gate-Source Voltage	V _{GS}	± 20	
Continuous Drain Current (T _J = 150 °C)	I _D	T _C = 25 °C	- 35 ^a
		T _C = 70 °C	- 25 ^a
		T _A = 25 °C	- 16 ^{b, c}
		T _A = 70 °C	- 9 ^{b, c}
Pulsed Drain Current (t = 300 μs)	I _{DM}	- 140	A
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C	
		T _A = 25 °C	- 12 ^{b, c}
Maximum Power Dissipation	P _D	T _C = 25 °C	38
		T _C = 70 °C	25
		T _A = 25 °C	3.5 ^{b, c}
		T _A = 70 °C	2.1 ^{b, c}
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150	°C
Soldering Recommendations (Peak Temperature) ^{d, e}		260	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^{b, f}	t ≤ 5 s	R _{thJA}	27	35	°C/W
Maximum Junction-to-Case (Drain)	Steady State	R _{thJC}	3.3	4.5	

Notes:

- Package limited.
- Surface mounted on 1" x 1" FR4 board.
- t = 2 s.
- See solder profile The DFN3X3 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.
- Maximum under steady state conditions is 80 °C/W.

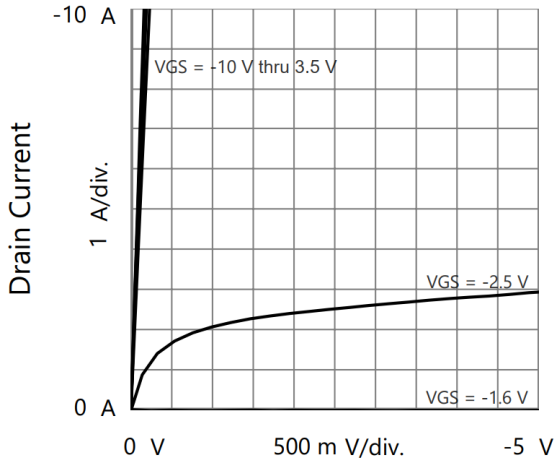
SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$	- 30			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = -250\text{ }\mu\text{A}$		- 11		mV/°C
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$		2.7			
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	- 1		- 3	V
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 8\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -30\text{ V}, V_{GS} = 0\text{ V}$			- 1	μA
		$V_{DS} = -24\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			- 10	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \leq -5\text{ V}, V_{GS} = -4.5\text{ V}$	- 35			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = -10\text{ V}, I_D = -10\text{ A}$		21	25	m Ω
		$V_{GS} = -4.5\text{ V}, I_D = -5\text{ A}$		30	35	
Forward Transconductance ^a	g_{fs}	$V_{DS} = -10\text{ V}, I_D = -10\text{ A}$		40		S
Dynamic^b						
Input Capacitance	C_{ISS}	$V_{DS} = -15\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		1440		pF
Output Capacitance	C_{OSS}		165			
Reverse Transfer Capacitance	C_{RSS}		155			
Total Gate Charge	Q_g	$V_{DS} = -15\text{ V}, V_{GS} = -10\text{ V}, I_D = -10\text{ A}$		22		nC
Gate-Source Charge	Q_{gs}		13			
Gate-Drain Charge	Q_{gd}		3.3			
Gate Resistance	R_g	$f = 1\text{ MHz}$		13		Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -15\text{ V}, R_L = 0.75\text{ }\Omega$ $I_D \cong -5\text{ A}, V_{GEN} = -4.5\text{ V}, R_g = 1\text{ }\Omega$		16		ns
Rise Time	t_r		17			
Turn-Off Delay Time	$t_{d(off)}$		21			
Fall Time	t_f		44			
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -15\text{ V}, R_L = 0.75\text{ }\Omega$ $I_D \cong -10\text{ A}, V_{GEN} = -10\text{ V}, R_g = 1\text{ }\Omega$		11		
Rise Time	t_r		15			
Turn-Off Delay Time	$t_{d(off)}$		30			
Fall Time	t_f		43			
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	$T_C = 25\text{ }^\circ\text{C}$			- 35	A
Pulse Diode Forward Current	I_{SM}				140	
Body Diode Voltage	V_{SD}	$I_S = -10\text{ A}, V_{GS} = 0\text{ V}$		- 0.7	- 1.2	V
Body Diode Reverse Recovery Time	t_{rr}	$I_F = -10\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$		40		ns
Body Diode Reverse Recovery Charge	Q_{rr}		20		nC	
Reverse Recovery Fall Time	t_a		15		ns	
Reverse Recovery Rise Time	t_b		26			

Notes:

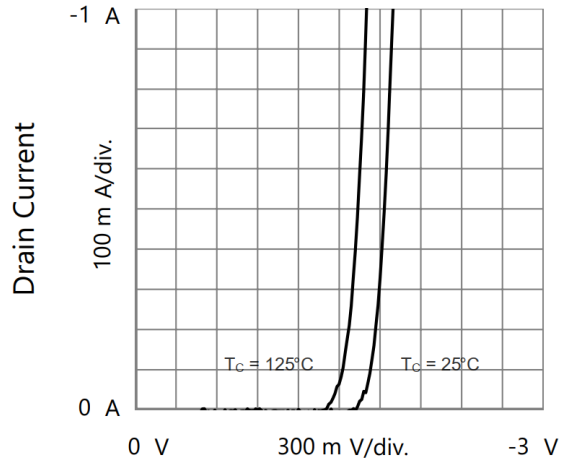
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
 b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

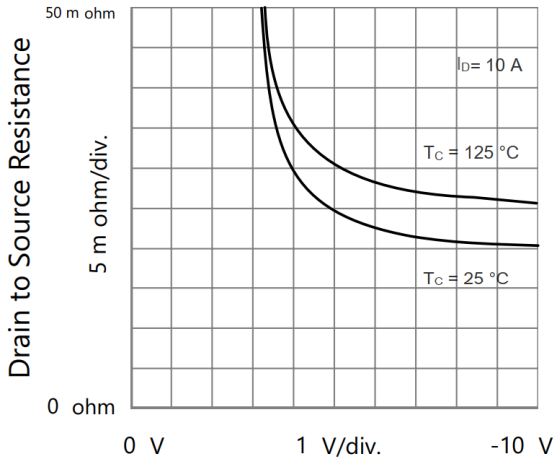
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



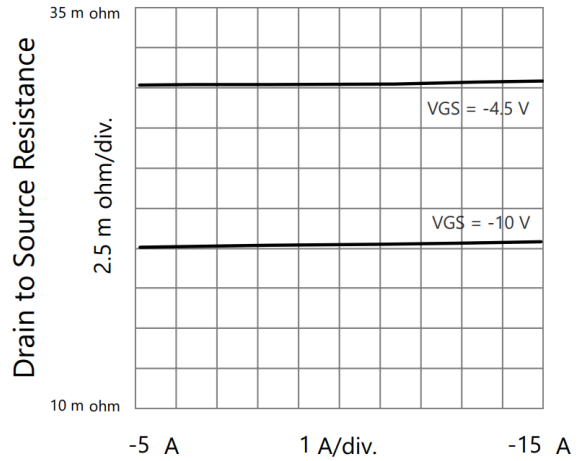
Drain to Source Voltage
Output Characteristics



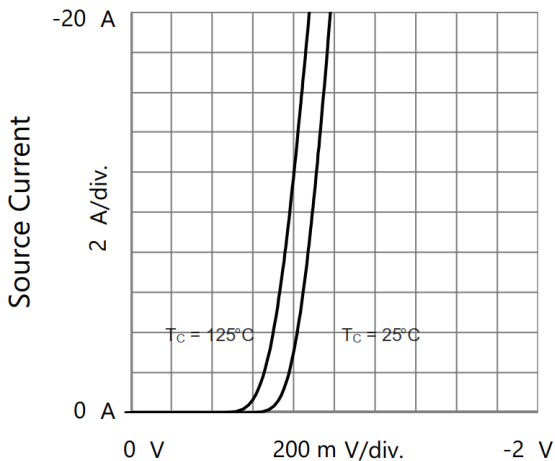
Gate to Source Voltage
Transfer Characteristics



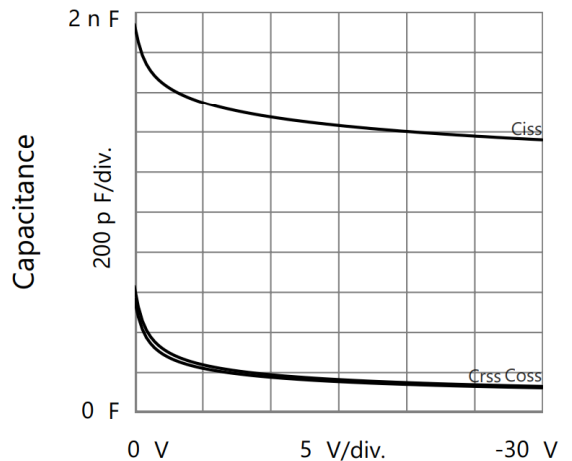
Gate to Source Voltage
Drain to Source Resistance vs. Gate to Source Voltage



Drain Current
Drain to Source Resistance vs. Drain Current

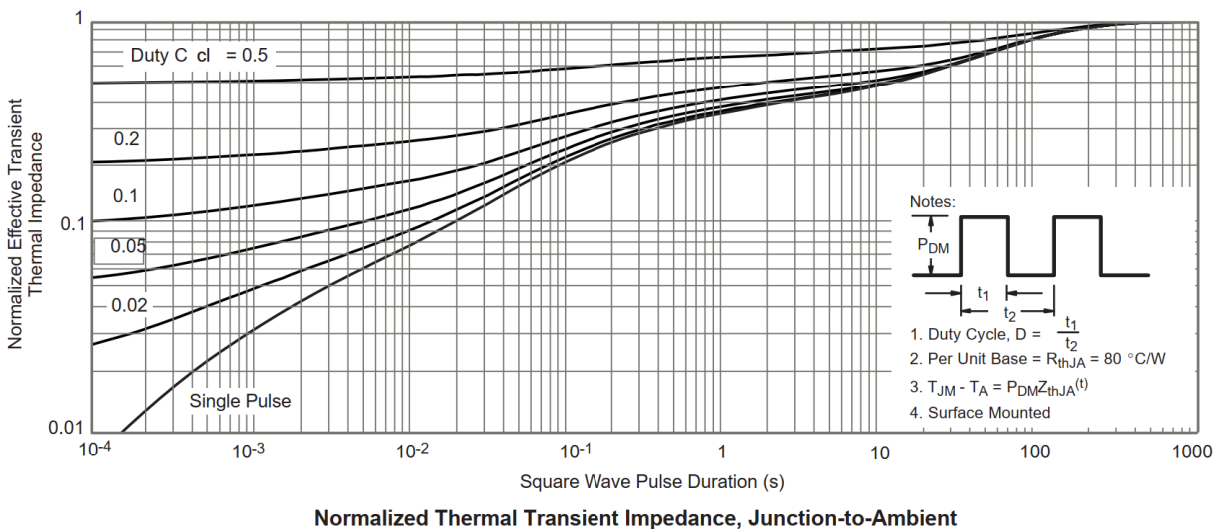
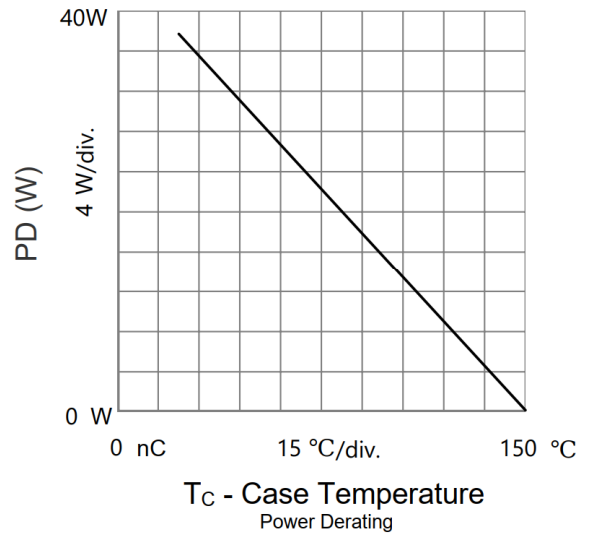
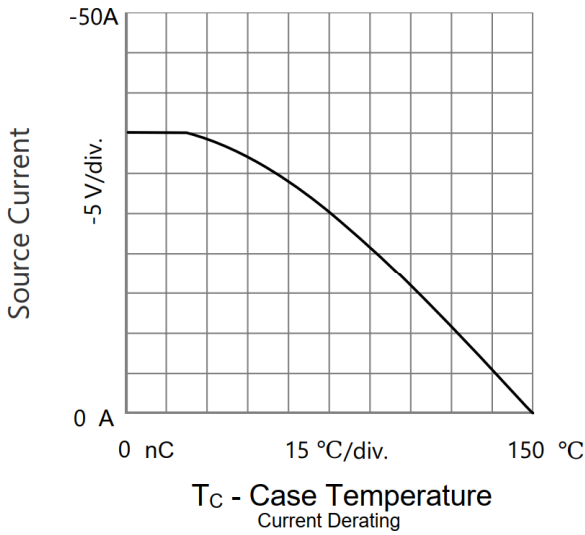
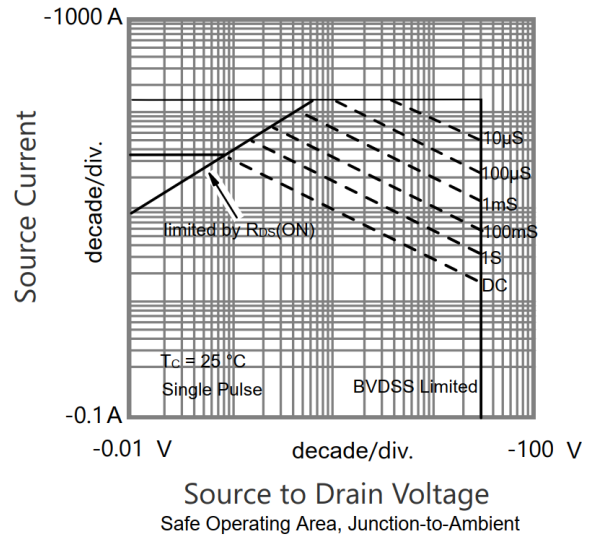
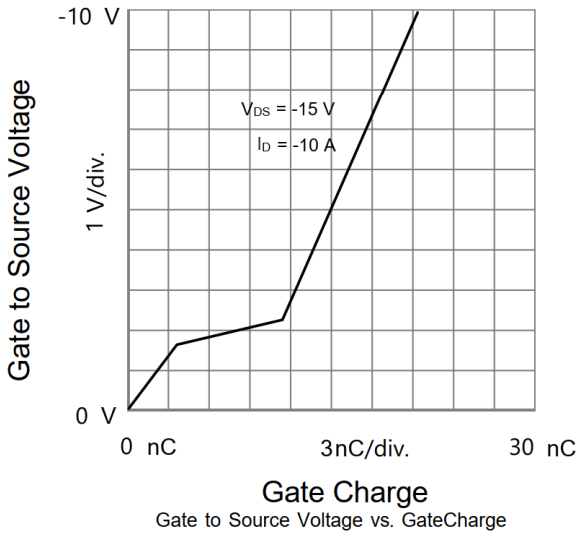


Source to Drain Voltage
Body Diode Forward Characteristics

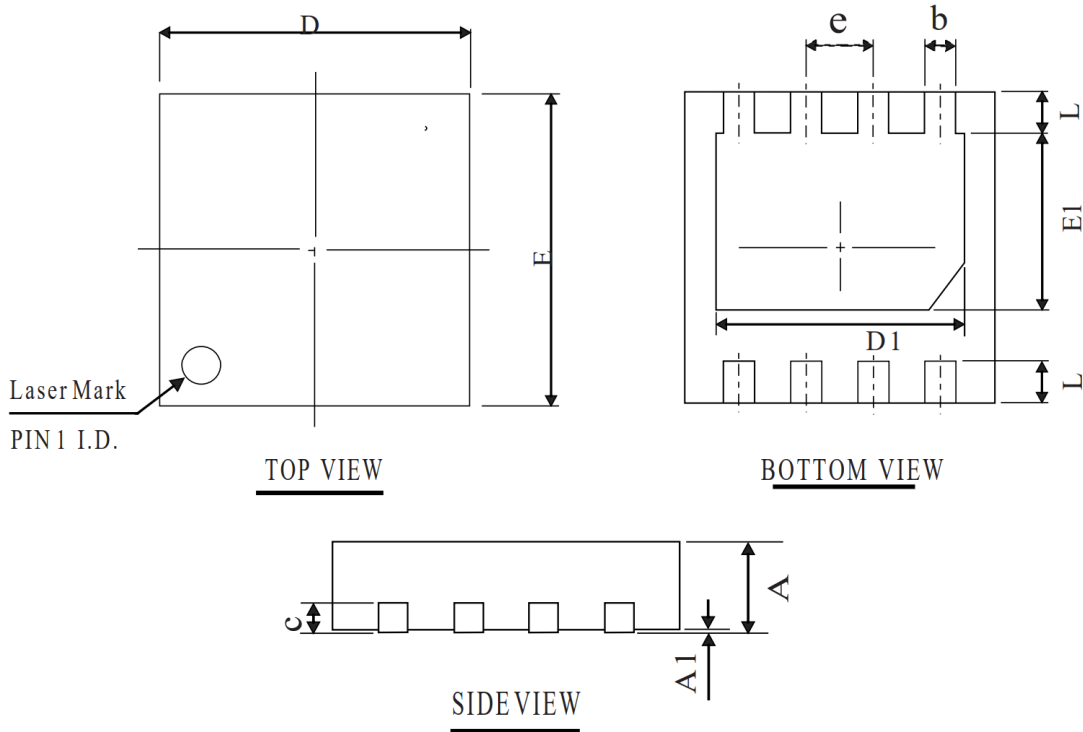


Drain to Source Voltage
Capacitances

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



DFN3*3-8L PACKAGE OUTLINE



COMMON DIMENSIONS (UNITS OF MEASURE=mm)

SYMBOL	MIN	NOM	MAX
A	0.60	0.75	0.90
A1	0.00	0.02	0.08
b	0.20	0.30	0.45
D	2.85	3.00	3.15
E	2.85	3.00	3.15
D1	2.10	2.40	2.70
E1	1.50	1.70	2.00
L	0.20	0.40	0.60
c	0.203 REF		
e	0.65 BSC		

OTHER DIMENSIONS

A	0.50	0.55	0.60
A	0.40	0.45	0.50

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